



AT 2815

BOX AF

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Kiyoshi IRINO**

Serial No.: **09/428,052**

Filed: **October 27, 1999**

Group Art Unit: **2815**

Examiner: **J. Diaz**

For: **METHOD OF FABRICATING A SEMICONDUCTOR DEVICE CONTAINING NITROGEN IN A GATE OXIDE FILM (AS AMENDED)**

AMENDMENT AFTER FINAL REJECTION

BOX AF

Commissioner for Patents
Washington, D.C. 20231

Date: November 13, 2001

TECHNOLOGY CENTER 2800
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Sir:

In response to the Office Action dated August 9, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 6 and 10 as follows:

Sub F1
6. (Three Times Amended) A method of fabricating a semiconductor device, comprising the steps of:

forming a gate oxide film on a substrate;

forming a gate electrode pattern on said gate oxide film;